

STTH120L04TV1

Ultrafast high voltage rectifier

Mian product characteristics

I _{F(AV)}	2 x 60 A
V _{RRM}	400 V
T _j (max)	150° C
V _F (typ)	0.83 V
t _{rr} (max)	50 ns

Features and benefits

- Ultrafast switching
- Low reverse current
- Low thermal resistance
- Reduces switching and conduction losses
- Package insulation voltage: 2500 V_{RMS}

ISOTOP STTH120L04TV1

Description

The STTH120L04TV1 uses ST 400 V technology and is specially suited for use in switching power supplies, welding equipment, and industrial applications, as an output rectification diode.

Order codes

Part number	Marking
STTH120L04TV1	STTH120L04TV1

Table 1. Absolute ratings (limiting values, per diode)

Symbol	Paran	Value	Unit		
V _{RRM}	Repetitive peak reverse voltage	400	V		
I _{F(RMS)}	RMS forward current	RMS forward current			Α
I _{F(AV)}	Average forward current $T_c = 115^{\circ} \text{ C } \delta = 0.5$ Per diode			60	Α
I _{FSM}	Surge non repetitive forward current $t_p = 10 \text{ ms sinusoidal}$			600	Α
T _{stg}	Storage temperature range			-55 to + 150	° C
T _j	Maximum operating junction temperature			150	° C

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Table 2. Thermal resistance

Symbol	ymbol Parameter		Value (max).	Unit
В	R _{th(j-c)} Junction to case		0.74	
hth(j-c)			0.42	°C/W
R _{th(c)}	Coupling		0.1	

When diodes 1 and 2 are used simultaneously:

 $\Delta \text{ Tj(diode 1)} = P(\text{diode 1}) \times R_{\text{th(j-c)}}(\text{Per diode}) + P(\text{diode 2}) \times R_{\text{th(c)}}$

Table 3. Static electrical characteristics (per diode)

Symbol	Parameter	Test conditions		Min.	Тур	Max.	Unit
I _R ⁽¹⁾	Reverse leakage	T _j = 25° C	V - V			50	μA
'R`	current	T _j = 125° C	$V_R = V_{RRM}$		50	500	μΑ
V _E ⁽²⁾	Forward voltage drop	T _j = 25° C	I _E = 60 A			1.2	V
V _F \ / Porward voltage drop	Forward voltage drop $T_j = 150^{\circ} \text{ C}$	1F = 00 A		0.83	1.0	V	

^{1.} Pulse test: $t_p = 5$ ms, $\delta < 2\%$

To evaluate the conduction losses use the following equation:

 $P = 0.8 \text{ x } I_{F(AV)} + 0.0033 I_{F^2(RMS)}$

Table 4. Dynamic characteristics (per diode)

Symbol	Parameter	Test conditions		Min	Тур	Max	Unit
+	Reverse recovery	T _i = 25° C	$I_F = 1 \text{ A} dI_F/dt = 50 \text{ A/}\mu\text{s}$ $V_R = 30 \text{ V}$		66	90	ns
t_{rr} time	$I_F = 1 \text{ A} dI_F/dt = 200 \text{ A/}\mu\text{s}$ $V_R = 30 \text{ V}$		36	50	120		
I _{RM}	Current	-	$I_F = 60 \text{ A}$ $V_R = 200 \text{ V}$ $dI_F/dt = 100 \text{ A}/\mu\text{s}$			15	Α
S _{factor}	Softness factor	T _j = 125° C	$I_F = 60 \text{ A}$ $V_R = 200 \text{ V}$ $dI_F/dt = 100 \text{ A/}\mu\text{s}$		0.4		
t _{fr}	Forward recovery time	T _j = 25° C	$I_F = 60 \text{ A}$ $V_{FMax} = 1.1 \text{ A}$ V_{Fmax}			600	ns
V _{FP}	Forward recovery voltage	T _j = 25° C	$I_F = 60 \text{ A}$ $dI_F/dt = 200 \text{ A/}\mu\text{s}$ $V_{FR} = 1.1 \text{ x } V_{Fmax}$		2.6		V

^{2.} Pulse test: $t_p = 380 \mu s$, $\delta < 2\%$

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Figure 1. Conduction losses versus average forward current (per diode)

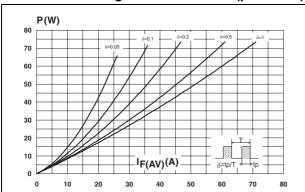


Figure 2. Forward voltage drop versus forward current (per diode)

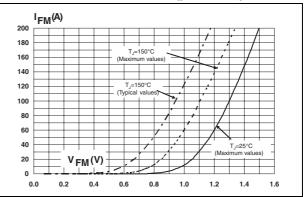
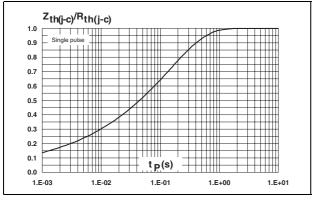


Figure 3. Relative variation of thermal impedance junction to case versus pulse duration

Figure 4. Peak reverse recovery current versus dl_F/dt (typical values, per diode)



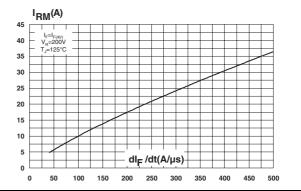


Figure 5. Reverse recovery time versus dl₋/dt (typical values, per diode)

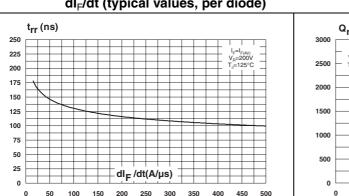
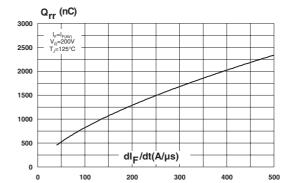


Figure 6. Reverse recovery charges versus dl_F/dt (typical values, per diode)

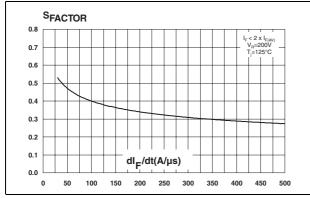


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Figure 7. Reverse recovery softness factor versus dl_F/dt (typical values, per diode)

Figure 8. Relative variations of dynamic parameters versus junction temperature



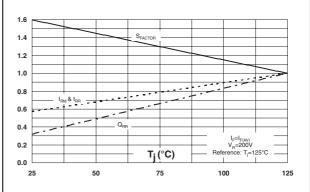
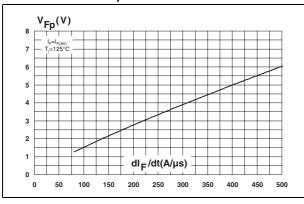


Figure 9. Transient peak forward voltage versus dl_F/dt (typical values, per diode)

Figure 10. Forward recovery time versus dI_F/dt (typical values, per diode)



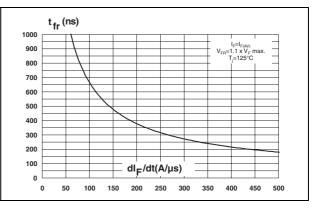
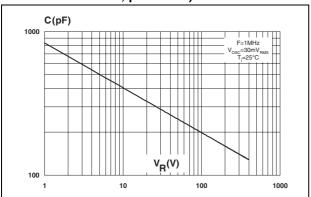


Figure 11. Junction capacitance versus reverse voltage applied (typical values, per diode)



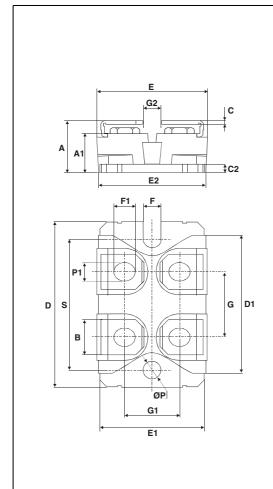
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2 Package information

Epoxy meets UL94, V0

Cooling method: by conduction (C)

Table 5. ISOTOP Dimensions



	Dimensions					
Ref.	Millim	neters	Inc	nes		
	Min.	Max.	Min.	Max.		
Α	11.80	12.20	0.465	0.480		
A1	8.90	9.10	0.350	0.358		
В	7.8	8.20	0.307	0.323		
С	0.75	0.85	0.030	0.033		
C2	1.95	2.05	0.077	0.081		
D	37.80	38.20	1.488	1.504		
D1	31.50	31.70	1.240	1.248		
Е	25.15	25.50	0.990	1.004		
E1	23.85	24.15	0.939	0.951		
E2	24.80 typ.		0.976 typ.			
G	14.90	15.10	0.587	0.594		
G1	12.60	12.80	0.496	0.504		
G2	3.50	4.30	0.138	0.169		
F	4.10	4.30	0.161	0.169		
F1	4.60	5.00	0.181	0.197		
Р	4.00	4.30	0.157	0.69		
P1	4.00	4.40	0.157	0.173		
S	30.10	30.30	1.185	1.193		

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Ordering information

3 Ordering information

Ordering type	Marking	Package	Weight	Base qty	Delivery mode
STTH120L04TV1	STTH120L04TV1	ISOTOP	27 g (without screws)	10 (with screws)	Tube

4 Revision history

Date	Revision	Description of Changes
11-Aug-2006	1	First issue

STTH120L04TV1

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